

EAST - [10626594.wsp:1]

File View Edit Tools Window Help

Drafts
 Pending
 Active
 L1: (46058) memory and (flip-flop or flip adj flop)
 L2: (1228) 1 and (inverter\$1 and \$1MOS and insulat\$3 and ca
 L3: (2) 2 and (access adj MOS and driver adj MOS)
 L5: (9) 1 and (access adj MOS and driver adj MOS)
 L4: (9) 1 and (access adj MOS and driver adj MOS)
 L6: (18) memory and (access adj MOS and driver adj MOS)
 L7: (2) 6 and (inverter\$1 and \$1MOS and insulat\$3 and capac
 Failed
 (0) 1 and inverter\$1 and \$1MOS and insulat\$3 and capacit\$3)
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DBs USPAT EPG JPO DERWENT IBM T Plurals

Default operator OR ☒ Highlight all hit terms initially

memory and (access adj MOS and driver adj MOS)

BR5 L ISAR Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6710412 B2	20040323	18	Static semiconductor memory device	257/369	257/368; 257/382;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6693360 B1	20040217	23	Static type semiconductor memory device	257/774	257/750; 257/758;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6597041 B2	20030722	28	Semiconductor static random access memory device	257/369	257/903
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6577021 B2	20030610	23	Static-type semiconductor memory device		257/904; 257/E27.099;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6479860 B2	20021112	25	Semiconductor memory device	257/315	257/303; 257/306;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6333542 B1	20011225	17	Semiconductor device and method of manufacturing the same	257/393	257/368; 257/379;
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6242806 B1	20010605	83	Semiconductor device and method of manufacturing thereof	257/755	257/756; 257/757;
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6198139 B1	20010306	17	Complementary MOS device	257/372	257/369; 257/E21.558;
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6180986 B1	20010130	21	Semiconductor device and method of manufacturing the same	257/368	257/350; 257/351;
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6069818 A	20000530	11	Semiconductor memory device having storage nodes doped with first and second	365/149	257/E21.647; 257/E21.66;
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5966324 A	19991012	53	Static semiconductor memory device driving bit line potential by bipolar transistor	365/177	257/E27.101; 365/155;